Supporting information

Expedient floating process for ultra-thin InGaZnO thin-film-transistors and their high bending performance

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Supporting information

Ref.	Substrate	Processing Temperature (°C)	Fabricated processing	μ_{FE} ($cm^2/V \cdot s$)	SS (V/dec)	V_{th} (V)	on/off ratio (A)
1	PDMS (80 μm)	150	Chemical	9.85	0.119	1.12	10^8
2	PI (10 μm)	200	Mechanical	15.1	0.25	0.9	~5 x 10^8
3	PI (18 μm)	250	Mechanical	7.15	0.23	0.56	10^9
4	PEN (125 μm)	150	Mechanical	15.5	0.20	4.1	2.2 x 10^8
This work	Parylene (10 μm)	150	Chemical	12.6	0.19	0.52	10^8

Table S1 Summary of substrate type, process condition, and calculated electrical performance values for the *a*-IGZO TFTs prepared on flexible plastic substrates, including the device studied in this work.

➡ Reference of supplementary data 1

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